

Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application:

Listing of Claims:

Claims 1 – 11 (Cancelled)

12. (Previously Presented) A method of fabricating a semiconductor device having a ferroelectric capacitor, comprising the steps of:

- forming an active device element on a substrate;
- forming an insulation film over said substrate to cover said active device element;
- forming a lower electrode layer of said ferroelectric capacitor over said insulation film, such that said lower electrode is formed on a layer containing Ti;
- forming a ferroelectric film on said lower electrode as a capacitor insulation film of said ferroelectric capacitor;
- crystallizing said ferroelectric film by applying a thermal annealing process in an O₂ atmosphere under a reduced total pressure in the range between 1 Torr and 40 Torr such that peeling of the ferroelectric film is substantially reduced;
- and
- forming an upper electrode layer on said ferroelectric film.

Claims 13 – 28 (Cancelled)